Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Sheet 1 of 8

Application Number	10/775,999
Filing Date	February 10, 2004
First Named Inventor	Faris
Group Art Unit	1792
Examiner Name	Binh X. Tran
Attorney Docket Number	Reveo-0179

U.S. PATENT DOCUMENTS

Examiner Initial	Doc. No.	Document Number	Date	Name	Class	Subclass	Filing Date (If Appropriate)
/BT/		4,309,225	05-Jan-82	Fan et al.	148	1.5	
		4,370,176	25-Jan-83	Bruel	148	1.5	
		4,371,421	01-Feb-83	Fan et al.	156	624	
		4,471,003	11-Sep-84	Cann	427	34	
		4,479,846	30-Oct-84	Smith et al.	156	603	
		4,500,563	19-Feb-85	Ellenberger et al.	427	38	
		4,585,945	29-Apr-86	Bruel et al.	250	492.2	
		4,816,420	28-Mar-89	Bozler et al.	437	2	
		4,837,182	06-Jun-89	Bozler et al.	437	82	
		4,846,931	11-Jul-89	Gmitter et al.	156	633	
		4,883,561	28-Nov-89	Gmitter et al.	156	633	
		5,273,616	28-Dec-93	Bozler et al.	156	603	
		5,362,682	08-Nov-94	Bozler et al.	437	226	
		5,374,564	20-Dec-94	Bruel	437	24	
		5,453,153	26-Sep-95	Fan et al.	117	2	
		5,559,043	24-Sep-96	Bruel	437	424	
		5,588,994	31-Dec-96	Bozler et al.	117	89	
		5,676,752	14-Oct-97	Bozler et al.	117	89	
		5,710,057	20-Jan-98	Kenney	437	62	
		5,714,395	03-Feb-98	Bruel	437	24	
		5,793,115	11-Aug-98	Zavracky et al.	257	777	
		5,845,123	01-Dec-98	Johnson et al.	395	377	
		5,877,070	02-Mar-99	Goesele et al.	438	458	
		5,882,987	16-Mar-99	Srikrishnan	438	458	
		5,897,939	27-Apr-99	Deleonibus	428	195	
		5,909,627	01-Jun-99	Egloff	438	406	
		5,920,764	06-Jul-99	Hanson et al.	438	4	
		5,933,750	03-Aug-99	Wilson et al.	438	455	
		5,976,953	02-Nov-99	Zavracky et al.	438	455	
		5,985,688	16-Nov-99	Bruel	438	53	
		5,993,677	30-Nov-99	Biasse et al.	216	36	
		5,994,207	30-Nov-99	Henley et al.	438	515	
		6,020,252	01-Feb-00	Aspar et al.	438	458	
		6,027,988	22-Feb-00	Cheung et al.	483	513	
		6,033,974	07-Mar-00	Henley et al.	438	526	
		6,054,363	25-Apr-00	Sakaguchi et al.	438	406	
		6,054,370	25-Apr-00	Doyle	438	456	
		6,059,877	09-May-00	Bruel	117	35	
		6,071,795	06-Jun-00	Cheung et al.	438	458	
		6,103,597	15-Aug-00	Aspar et al.	438	458	
		6,137,110	24-Oct-00	Pellin et al.	250	423	
/BT/		6,146,979	14-Nov-00	Henley et al.	438	458	

Examiner Signature	/Binh Tran/	Date Considered	11/14/2008

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /BT/

Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Sheet 2 of 8

Application Number	10/775,999
Filing Date	February 10, 2004
First Named Inventor	Faris
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Examiner Name	Binh X. Tran
Attorney Docket Number	Reveo-0179

U.S. PATENT DOCUMENTS

Examiner Initial	Doc. No.	Document Number	Date	Name	Class	Subclass	Filing Date (If Appropriate)
/BT/		6,155,909	05-Dec-00	Henley et al.	451	39	
		6,159,323	12-Dec-00	Joly et al.	156	241	
		6,159,824	12-Dec-00	Henley et al.	438	455	
		6,159,825	12-Dec-00	Henley et al.	438	460	
		6,162,705	19-Dec-00	Henley et al.	438	478	
		6,184,060	06-Feb-01	Siniaguine	438	106	
		6,184,111	06-Feb-01	Henley et al.	438	514	
		6,187,110	13-Feb-01	Henley et al.	148	33.2	
		6,190,937	20-Feb-01	Nakagawa et al.	438	67	
		6,190,998	20-Feb-01	Bruel et al.	438	407	
		6,191,007	20-Feb-01	Matsui et al.	438	459	
		6,204,151	20-Mar-01	Malik et al.	438	460	
		6,214,733	10-Apr-01	Sickmiller	438	691	
		6,221,738	24-Apr-01	Sakaguchi et al.	438	455	
		6,221,740	24-Apr-01	Bryan et al.	438	458	
		6,221,774	24-Apr-01	Malik	438	690	
		6,225,190	01-May-00	Bruel et al.	438	458	
		6,225,192	01-May-00	Aspar et al.	438	460	
		6,232,136	15-May-01	Zavracky et al.	438	30	
		6,387,736	May 2002	Cao et al.	438	149	
		6,309,945	Oct 2001	Sato	437	409	
		6870361	3/22/2005	Chopra, et al.	324	158.1	
		6869764	3/22/2005	Williams, et al.	435	006	
		6772070	8/3/2004	Gilmanshin et al.	702	019	
		6762059	7/13/2004	Chan, et al	436	164	
		6762050	7/13/2004	Fukushima , et al.	435	287.9	
		6762025	7/13/2004	Cubicciotti	435	006	
		6753147	6/22/2004	Vogelstein, et al	435	006	
		6746594	6/8/2004	Akeson , et al.	205	777.5	
		6696022	2/24/2004	Chan, et al	422	099	
		6673615	1/6/2004	Denison , et al.	436	002	
		6627067	9/30/2003	Branton , et al.	205	778	
		6617113	9/9/2003	Deamer	435	006	
		6537747	3/25/2003	Mills, et al.	435	006	
		6528266	3/4/2003	Meade et al.	435	006	
		6524829	2/25/2003	Seeger	435	0912	
		6495323	12/17/2002	Kayyem et al.	435	006	
		6482639	11/19/2002	Snow et al.	435	2872	
		6468742	10/22/2002	Nerenberg et al.	435	006	
		6465193	10/15/2002	Akeson , et al.	435	007.1	
		6451996	9/17/2002	Drmanac et al.	536	0243	
/BT/		6451996	9/17/2002	Drmanac et al.	536	0243	

Examiner Signature	/Binh Tran/	Date Considered	11/14/2008

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Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Sheet 3 of 8

Application Number	10/775,999
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Group Art Unit	1792
Examiner Name	Binh X. Tran
Attorney Docket Number	Reveo-0179

U.S. PATENT DOCUMENTS

Examiner Initial	Doc. No.	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
/BT/		6428959	8/6/2002	Deamer	435	006	
		6403311	6/11/2002	Chan; Eugene Y.	435	006	
		6391624	5/21/2002	Megerle; Clifford A.	435	2872	
		6362002	3/26/2002	Denison , et al.	436	002	
		6355420	3/12/2002	Chan	435	006	
		6277576	8/21/2001	Meade et al.	435	006	
		6267872	7/31/2001	Akeson , et al.	205	775	
		6263286	7/17/2001	Gilmanshin et al.	702	019	
		6210896	4/3/2001	Chan	435	006	
		6106777	8/22/2000	Fujita et al	422	050	
		6063573	5/16/2000	Kayyem	435	006	
		6015714	1/18/2000	Baldarelli , et al.	436	002	
		5969345	10/19/1999	Williams et al.	250	234	
		5882856	3/16/1999	Shuber.	435	006	
		5795782	8/18/1998	Church et al.	436	002	
		2001014850A1	8/16/2001	Gilmanshin et al.	702	019	
		2002013663A1	1/31/2002	Erlich	702	019	
		2002094519A1	7/18/2002	McKernan et al.	435	004	
		2002098526A1	7/25/2002	Bamdad	435	0079	
		2002110818A1	8/15/2002	Chan	435	006	
		2002177695A1	11/28/2002	Grinstaff et al.	536	0231	
		2003059822A1	3/27/2003	Chan et al.	435	006	
		2003064366A1	4/3/2003	Hardin et al.	435	006	
		2003064400A1	4/3/2003	Williams	435	006	
		2003077631A1	4/24/2003	Kucharczyk	435	006	
		2003143549A1	7/31/2003	Yang et al.	435	006	
		2003148328A1	8/7/2003	Kayyem et al.	435	006	
		2003162181A1	8/28/2003	Yang et al.	435	006	
		2003162214A1	8/28/2003	Heller et al	435	006	
		2003170677A1	9/11/2003	Meade et al.	435	006	
		2003186255A1	10/2/2003	Williams et al	435	006	
		2003190647A1	10/9/2003	Odera, Raj	435	006	
		2003215864A1	11/20/2003	Gilmanshin et al.	435	006	
		2003224356A1	12/4/2003	Knoll et al.	435	006	
		2004009612A1	1/15/2004	Zhao et al.	436	501	
		2004043506A1	3/4/2004	Haussecker et al.	436	180	
		2004048241A1	3/11/2004	Freeman et al.	435	005	
		2004072200A1	4/15/2004	Rigler et al.	435	006	
		2004101891A1	5/27/2004	Rigler et al.	435	006	
		2004133359A1	7/8/2004	Erhlich	702	020	
/BT/		2004166025A1	8/26/2004	Chan et al.	422	099	
		2004214211A1	10/28/2004	Gilmanshin et al.	435	006	

Examiner Signature	/Binh Tran/	Date Considered	11/14/2008

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /BT/

Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Sheet 4 of 8

Application Number	10/775,999
Filing Date	February 10, 2004
First Named Inventor	Faris
Group Art Unit	1792
Examiner Name	Binh X. Tran
Attorney Docket Number	Reveo-0179

U.S. PATENT DOCUMENTS

Examiner Initial	Doc. No.	Document Number	Date	Name	Class	Subclass	Filing Date (If Appropriate)
/BT/		2005042665A1	2/24/2005	Gilmanshin	435	006	
		2005064449A1	3/24/2005	Knoll et al.	435	006	
		2002016810	11/14/2002	Jackson	438	172	
		20020191884A1	12/19/2002	Letant et al.	385	012	
		20030040173	2/27/2003	Fonash et al.	438	622	
		20030049177	3/13/03	Smith et al.	506	029	
		20030164297A1	9/4/2003	Day et al.	204	469	
		20030165806A1	9/4/2003	Paushc	435	004	
		20050136419	6/23/2005	Lee	435	006	
/BT/		20050202668	9/15/2005	McCarty	438	623	

FOREIGN PATENT DOCUMENTS

Examiner Initial		Document Number	Date	Country	Class	Subclass	Translation YES	Translation NO
/BT/		EP0355913A1	28-Feb-90	Europe				
		WO 95/20824A1	3-Aug-95	PCT				
		WO 98/20543A2	14-May-98	PCT				
		WO 98/33209	30-Jul-98	PCT				
		WO 99/05711A1	4-Feb-99	PCT				
		WO 99/08316A1	18-Feb-99	PCT				
		WO 99/35674A1	15-Jul-99	PCT				
		WO 99/39377A1	5-Aug-99	PCT				
		WO 99/66559A1	23-Dec-99	PCT				
		WO 00/03429A1	20-Jan-00	PCT				X
		WO 00/24059A1	27-Apr-00	PCT				X
		WO 00/24054A1	27-Apr-00	PCT				X
		WO 00/46847A1	10-Aug-00	PCT				
		WO 00/48238A1	17-Aug-00	PCT				
		EP01045448A1	18-Oct-00	Europe				
		WO 00/75995A1	14-Dec-00	PCT				
		WO 00/75968A1	14-Dec-00	PCT				
		WO 01/03172A1	11-Jan-01	PCT				
		WO 01/03171A1	11-Jan-01	PCT				
		JP 63-155731	Jun 1988	JP				X
		0938129	25-08-1999	EP				
		2771852	04-06-1999	FR				
		0793263	03-09-1997	EP				
/BT/		2758907	31-07-1998	FR				

Examiner Signature	/Binh Tran/	Date Considered	11/14/2008

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Substitute for form 1449A/PTO **INFORMATION DISCLOSURE STATEMENT BY APPLICANT**		
	Application Number	10/775,999
	Filing Date	February 10, 2004
	First Named Inventor	Faris
	Group Art Unit	1792
	Examiner Name	Binh X. Tran
Sheet 5 of 8	Attorney Docket Number	Reveo-0179

OTHER DOCUMENTS ***(Including Author, Title, Date, Pertinent Pages, Etc.)***		
/BT/		Miller, D.L., et. al., "GaAs Peeled Film Solar Cells," Rockwell International, pp. 1-45, March 15, 1980-Dec. 31, 1981
		Fan, J.C.C., "Thin Films of III-V Compounds and Their Applications," Journal de Physique, 43, pp. C1-327, (1982)
		Konagai, Makoto, et al., "High Efficiency GaAs Thin Film Solar Cells by Peeled Film Technology", Journal of Crystal Growth, vol. 45, pp. 277-280, 1978
		Bower, R.W., et al., "Aligned Wafer Bonding: A Key to Three Dimensional Microstructures," Journal of Electronic Materials, Vol. 20, No. 5, pp. 383-387, 1991
		Lee, K.Y., et al., "Fabrication of Ultrasmall Devices on Thin Activ GaAs Membranes," J. Vac. Sci. Technol.B5 (1), pp. 322-325, 1987
		Camperi-Ginestet, C., "Alignable Epitaxial Liftoff of GaAs Materials With Selective Deposition Using Polyimide Diaphragms," IEEE Transactions Photonics Technology Letters, pp. 1123-1126, Dec. 12, 1991
		Hargis, M.C., et al., "Epitaxial Lift-Off GaAS/A1GaAs Metal - Semiconductor-Metal Photodetectors with Back Passivaton," IEEE Photonics Technology Letters, Vol. 5, No. 10, pp. 1210-1212, 1993
		Schnitzer, L., et al., "Ultra-High Efficiency Light-Emitting-Diode Arrays," IEEE Transactions on Electron Devices, Vol. 40, No. 11, pp. 2108-2109, Nov. 1993
		Zhang, L., et. al., "Low-energy Separation By Implantation of Oxygen Structures Via Plasma Source Ion Implantation," Applied Physics Lett., Vol. 65, No. 8, pp. 962-964, Aug. 22, 1994
		Bengtsson, S., et al., "Silicon on Aluminum Nitride Structures Formed by Wafer Bonding," Proceedings IEEE International SOI Conference, pp. 35 - 36, Oct. 1994
		Zahraman, K., et al., "Epitaxial Lift-Off in Photovoltaics: Ultra Thin Al0.2Ga0.8AsCell in a Mechanically Stacked (AL, Ga)As/Si Tandem," First WCPEC, pp. 1898- 1901, Dec. 5-9 1994
		Young, Paul G., et al., "RF Control of Epitaxial Lift-Off PHEMT's Under Backside Illumination," IEEE Journal of Quantum Electronics, Vol. 30, No. 8, pp. 1782-1786, Aug. 1994
		Hageman, P.R., et al., "Re-use of GAAS Substrates for Epitaxial Lift-Off III-V Solar Cells," IEEE, pp. 1910-1913, 1994
		Wilkinson, Scott T., et al., "Integration of Thin Film Optoelectronic Devices onto Micromachined Movable Platforms," IEEE Photonics Technology Letters, Vol. 6, No. 9, 1115-1118, Sept. 1994
		Callahan, J., et al., "Alignable Lift-Off Transfer of Device Arrays Via A Single Polymeric Carrier Membrane," IEEE, pp.1274 - 1277, 1995
		Spiering, Vincent L., et al., "Sacrificial Wafer Bonding for Planarization After Very Deep Etching," Journal of Microelectromechanical Systems, Vol. 4, No. 3, pp. 151-157, Sept. 1995
/BT/		Bhattacharya, D., et al., "Optical Mixing in Epitaxial Lift-Off Pseudomorphic HEMT's," IEEE Photonics Technology Letters, Vol. 7, No. 10, pp. 1171-1173, Oct. 1995

Examiner Signature	/Binh Tran/	Date Considered	11/14/2008

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /BT/

Substitute for form 1449A/PTO **INFORMATION DISCLOSURE STATEMENT BY APPLICANT**		
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	Filing Date	February 10, 2004
	First Named Inventor	Faris
	Group Art Unit	1792
	Examiner Name	Binh X. Tran
Sheet 6 of 8	Attorney Docket Number	Reveo-0179

OTHER DOCUMENTS ***(Including Author, Title, Date, Pertinent Pages, Etc.)***		
/BT/		Hohkawa, K., et al., "Fabricatoin of Surface Acoustic Wave Semiconductor Coupled Devices Using Epitaxial Lift-off Technology," IEEE Ultrasonics Symposium, pp.401-404, 1995
		Fan, J.C., et al., "AlGAAs/GaAs Heterojunction Bipolar Transistors on Si Substrate Using Epitaxial Lift-Off," IEEE Electron Device Letters, Vol. 16, No. 9, pp. 393-395, Sept. 1995
		Shah, Divyang M., et al., "Epitaxial Lift-Off GaAs HEMT's," IEEE Transactions on Electron Devices, Vol. 42, No. 11, pp. 1877-1881, Nov. 1995
		Morf, T., et al., Integrating Optical Receiver Transplanted by Epitaxial Lift Off," IEEE, pp. 189-192, 1995
		Herrscher, M., "Epitaxial Liftoff In GaAs/InP MSM Photodetectors on Si," Electronics Letters, Vol. 31, No. 16, pp. 1383-1384, Aug. 3. 1995
		Omnes, et al., "Substrate Free GaAs Photovoltaic Cells on Pd-Coated Silicon with a 20% AM1.5 Efficiency," IEEE Transactions on Electron Devices, Vol. 43, No. 11, pp. 1806 - 1811 (Nov. 1996)
		Jokerst. N.M., et al., "Thin-Film Multimaterial Optoelectronic Integrated Circuits," IEEE Transactions on Components, Packaging, and Manufacturing Technology - Part B, Vol. 19, No. 1, pp.97-105, Feb. 1996
		Tong, Q.Y., et al., "Feasiblity Study of VLSI Device Layer Transfer by CMP PETEOS Direct Bonding," Proceedings 1996 IEEE International SOI Conference, pp. 36-37, Oct. 1996
		Dohle, G. Rainer, et al., "A New Bonding Technique for Microwave Devices," IEEE Transactions on Components, Packaging, and Manufacturing Technology - Part B, Vol. 19, No. 1, pp. 57-63, Feb. 1996
		Yazawa, Y., et al., "Three-Junction Solar Cells Comprised of a Thin-Film GainP/GaAs Tandem Cell Mechanically Stacked on a Si Cell," IEEE, pp. 899-902, Sept. 30 - Oct. 3, 1997
		Yablonovitch, E., et al., "Extreme Selectivity in the Lift-Off of Epitaxial GaAs Films", Appl. Phys. Lett., 51 (26), pp. 2222- 2224, Dec. 28, 1997
		Chun, Carl, et al., "Integrated 1.55 um Receivers Using GaAs MMICS and Thin Film InP Detectors," IEEE, pp. 47-50, 1998
		Yun, C.H., et al., "Transfer of Patterned Ion-Cut Silicon Layers," Applied Physics Lett., Vol. 73, No. 19, pp. 2772-2774, Nov. 9, 1998
		Geppert, Linda, "Solid State," IEEE Spectrum, pp. 52-56, Jan. 1999
		Pasquareillo, D. et al., "Mesa-Spacers: Enabling Non-Destructive Measurements of Surface Energy in Room Temperature Wafer Bonding," as published in *Semiconductor Wafer Bonding: Science, Technology and Applications,* Electrochemical Society Proceedings, Vol. 99-35, pp. 110-118, Fall 1999
/BT/		Bagdahn, J. et al., "Lifetime Properties of Wafer-Bonded Components Under Static and Cyclic Loading ," as published in *Semiconductor Wafer Bonding: Science, Technology, and Applications,* Electrochemical Society Proceeding, Vol. 99-35, pp. 129-135, Fall 1999

Examiner Signature	/Binh Tran/	Date Considered	11/14/2008

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /BT/

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	Examiner Name	Binh X. Tran
Sheet 7 of 8	Attorney Docket Number	Reveo-0179

OTHER DOCUMENTS ***(Including Author, Title, Date, Pertinent Pages, Etc.)***		
/BT/		Beggans, M., et al., "Oxidation Effect on Microcontamination and Bondability of Ultrathin Silicon Wafers," as published in *Semiconductor Wafer Bonding: Science, Technology, and Applications,* Electrochemical Society Proceeding, Vol. 99-35, pp. 137-145, Fall 1999
		Pasquariello, D., et al., "Oxidation and Induced Damages in Oxygen Plasma In-Situ Wafer Bonding," as published in *Semiconductor Wafer Bonding: Science, Technology, and Applications*, Electrochemical Society Proceedings, Vol. 99-35, pp. 169-177, Fall 1999
		Bagdahn, J. et al., "Measurement of the Local Strength Distribution of Directly Bonded Silicon Wafers Using the Micro-Chevron-Test, as published in *Semiconductor Wafer Bonding: Science, Technology, and Applications,* Electrochemical Society Proceedings, Vol. 99-35, pp. 218-231, Fall 1999
		Andreas, P. et al., "Room Temperature Covalent Bonding: Effect on Interfacial Properties," as published in Semiconductor Wafer Bonding: Science, Technology, and Applications, Electrochemical Society Proceedings, Vol. 99-35, pp. 232-243, Fall 1999.
		Kopper-Schmidt, P., et al., "Recent Developments in Adhesion-Enhanced High-Vacuum Bonding By In Situ Plasma Surface Precleaning," as published in *Semiconductor Wafer Bonding: Science, Technology, and Applications*, Electrochmeical Society Proceedings, Vol. 99-35, pp. 259-273, Fall 1999
		Krauter, G. et al., "Interface Chemistry of Tailor-Made Monolayers for Low-Temperature Wafer Bonding," as published in *Semiconductor Wafer Bonding: Science, Technology, and Applications*, "Electrochemical Society Proceedings, Vol. 99-35, pp. 275-281, Fall 1999
		Wiegand, M. et al., "Effect of O2 Plasma Pretreatment on the Bonding Behavior of Silicon (100) Wafers," as published in *Semiconductor Wafer Bonding: Science, Technology, and Applications,* Electrochemical Society Proceedings, Vol. 99-35, pp. 282-291, Fall 1999
		Reiche, M. et al., "Plasma Activation for Low-Temperature Wafer Direct Bonding," as published in *Semiconductor Wafer Bonding: Science, Technology, and Applications*, Electrochemical Society Proceeding, Vol. 99-35, pp. 292-301, Fall 1999
		Tong, Q.T., "Wafer Bonding and Layer Transfer for Microsystems: An Overview," as published in *Semiconductor Wafer Bonding: Science, Technology, and Applications*, Electrochemical Society Proceedings, Vol. 99-35, pp. 1-39, Fall 1999
		Reiche, M. et al., "Bonding Behaviour of Different Interfacial Layers," as published in *Semiconductor Wafer Bonding: Science, Technology, and Applications,* Electrochemical Society Proceedings, Vol. 99-35, pp. 100-105
		Labossiere, et al., "Characterization of Wafer Bond Toughness," as published in *Semiconductor Wafer Bonding: Science, Technology, and Applications, Electrochemical Society Proceedings*, Vol. 99-35, pp. 338-349, Fall 1999
/BT/		Syms, R.R.A. et al., "3-D Self Assembly of Opto-Mechanical Structures Using Bonded Silicon-on-Insulator," as published in *Semiconductor Wafer Bonding: Science, Technology, and Applications*, Electrochemical Society Proceedings, Vol. 99-35, pp. 110-118, Fall 1999

Examiner Signature	/Binh Tran/	Date Considered	11/14/2008

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /BT/

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Sheet 8 of 8	Attorney Docket Number	Reveo-0179

OTHER DOCUMENTS ***(Including Author, Title, Date, Pertinent Pages, Etc.)***		
/BT/		Chu, Paul K. et al., "Microcavities Formed by Hydrogen or Helium Plasma Immersion Ion Implntation," IEEE, pp. 1238-1241
		King, Tsu-Jae, "Poly-Si TFTs for Plastic Substrates," Information Display, pp. 24-26, April 2001
		Williams, David, et al., "Microsystems Mature," Spie's Magazine, pp. 27-29, May 2001
		Marcinkevicius, Andrius et al., "Femtosecond Laser-Assisted Three-Dimensional Microfabrication in Silica," Optics Letters, Vol. 26, No. 5, pp. 277-279, March 1, 2001
		Jokerst, N.M., "Epitaxial Liftoff of GaAs Detectors Onto Silicon Integrated Circuits," pp. 664 – 665
		Tong, Q-Y., et al., "Wafer Bonding of Si With Dissimilar Materials," pp. 524 - 526
		Basco, Ricardo, et al., "Monolithic Integration of a 94GHz AlGAAs/GaAs 2 DEG Mixer on Quartz Substrate by Epitaxial Lift-Off," Department of Electrical and Computer Engineering University of Massachusetts, Amherst MA, pp. 38-39 *(that is the only info.)*
		Akatsu T., et al., "Wafer Bonding of Compoun Semiconductors Using Atomic Hydrogen," Electrochemical Society Proceedings, Vol. 99-35, pp. 60-419
		Schaffer, Chris B., et al., "Micromachining Using Ultrashort Pulses From a Laser Oscillator,"
		Huang, L-J., et al., "Critical Bonding Energy Required for Hydrogen-Implantation Induced Layer Splitting,"Electrochemical Society Proceedings, Vol. 99-35, pp. 68-77,
		Klem, J.F., et al., "Characteristics of Lift-Off Fabricated A1GaAs/InGaAs Single-Strained-Quantum-Well Structures on Glass and Silicon Substrates,"
		" Selective Wafer Bonding by Surface Roughness Control" by C. Gui, et al. published in Journal of the Electrochemical Society, 148 (4) G225-G228 2001 pp. G225-G228
		International Search Report Dated 06/10/03 for PCT/US0215864
		International Preliminary Report on Patentability Dated 02/04/2004 for PCT/US0215864
		International Preliminary Report on Patentability Dated 02/05/2008 for PCT/US2006/030849
		International search report Dated May 18, 2007 for PCT/US2006/030849
		International search report Dated October 25, 2005 for PCT/US04/03770
/BT/		International Preliminary Report on Patentability Dated 12/01/2005 for PCT/US04/03770

Examiner Signature	/Binh Tran/	Date Considered	11/14/2008

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